

isc Silicon PNP Transistor

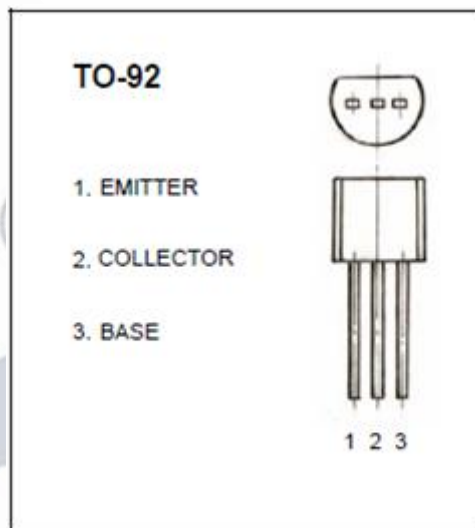
2SA1013

DESCRIPTION

- High Voltage and High Current
V_{ceo}=-160V(Min.)
- Excellent hFE Linearity
- Low Noise
- Complement to Type 2SC2383
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio frequency general purpose amplifier Applications
- Driver stage amplifier applications.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-160	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-1	A
I _B	Base Current	-500	mA
P _C	Collector Power Dissipation @T _c =25°C	900	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

isc Silicon PNP Transistor**2SA1015****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$; $I_B = -50\text{mA}$			-1.5	V
I_{CBO}	Emitter Cutoff Current	$V_{CB} = -150\text{V}$; $I_E = 0$			-1.0	μA
I_{EBO}	Collector Cutoff Current	$V_{EB} = -6\text{V}$; $I_C = 0$			-1.0	μA
h_{FE}	DC Current Gain	$I_C = -200\text{mA}$; $V_{CE} = -5\text{V}$	60		200	

◆ **h_{FE} Classifications**

R	O
60-120	100-200